

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	3209	hafnium adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/14 18:05
S2	4009	ald or atomic adj layer adj deposition	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/03 18:19
S3	0	hafnium adj oxide1 and (ald or atomic adj layer adj deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/30 06:16
S4	264	(hafnium adj oxide) and (ald or atomic adj layer adj deposition)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/30 06:16
S5	589910	capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/30 06:17
S6	120	((hafnium adj oxide) and (ald or atomic adj layer adj deposition)) and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/30 06:42
S7	45	ruthenium and ((hafnium adj oxide) and (ald or atomic adj layer adj deposition))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/30 06:42
S8	6536	ald or atomic adj layer adj deposition	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/23 09:10
S9	8045	purge and graph	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/23 09:10

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S10	281	S8 and S9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/23 09:10
S11	12482	capacitor adj dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/23 09:10
S12	46	S10 and S11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/23 09:10
S13	7740	ald or atomic adj layer adj deposition	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/03 18:19
S14	13	tantalum adj penta-ethoxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/03 18:20
S15	8704	ald or atomic adj layer adj deposition	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/27 13:37
S16	683186	capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/27 13:37
S17	2576	S15 and S16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/27 13:37
S18	8462	metal adj oxide adj film	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/27 13:37

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S19	152	S17 and S18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/27 13:37
S20	1045	dram and capacitor and ild	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/30 09:14
S21	551	(anneal or annealing) near4 (passivate or passivating or passivation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/30 09:18
S22	5	S20 and S21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/30 09:16
S23	80	(anneal or annealing) near4 ild	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/30 09:18
S24	23	S20 and S23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/30 09:18
S25	2143	cylindrical adj capacitor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/14 08:20
S26	12290	ald or atomic adj layer adj deposition	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/14 08:21

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S27	74	S26 and S25	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/14 08:21
S28	0	(first adj stage and (material adj gas near4 oxide) and vapor and reaction adj chamber and cylindrical adj trench).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/14 16:14
S29	121	(438/452).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2007/07/14 16:17
S30	120	(438/454).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2007/07/14 16:21
S31	135	(438/391).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2007/07/14 16:21
S32	54	257/e21.546	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/14 18:10
S33	0	257/e21.350	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/14 18:10
S34	19	257/e21.396	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/14 18:11

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S35	19	257/e21.651	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/14 18:11
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